Amendments to the Specification

On page 1 of the specification, please replace the paragraph following the heading "RELATED PATENT APPLICATION" with the following paragraph:

"This application is related to [the following: Docket #TS03-346,] <u>U.S. Patent</u>

<u>Application Ser. No. 10/987,713</u> [______], <u>filed on 11/12/2004</u>, [_____;] <u>which is assigned to a common assignee."</u>

On pages 14-15 of the specification, please replace the paragraph beginning "Referring to FIG. 5 ..." with the following paragraph:

"Referring to FIG. 5, a second ECP process is performed to deposit a second metal layer 19 that is preferably copper on the first metal layer 18. In one embodiment, the second ECP process is performed in a second work piece with an electrolyte solution that does not contain HCl or a carbon based additive as described in the related TSMC U.S. patent application Ser. No. 10/987,713, filed 11/12/2004TS03-346, herein incorporated by reference, and thereby avoids incorporating Cl and C contaminants in the second metal layer 19. Preferably, the second ECP process involves the same electrolyte solution and work piece that was employed in the first ECP process. The second ECP process is performed at a temperature of 10°C to 20°C and is comprised of two steps. The first step has a second current density of about 20 to 60 mA/cm² and preferably 40 mA/cm² that is applied until the second metal layer 19 fills the trench 15. This first step of the second ECP process is referred to by the inventors as ECP I40 and is continued for a period of about 30 to 50 seconds and has a metal deposition rate of about 150 Angstroms per minute."